

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	121	(semiconductor substrate wafer silicon) and (gate same (field adj plate) same align\$8)	US-PGPUB; USPAT	OR	ON	2005/04/18 12:11
L2	22	((semiconductor substrate wafer silicon) and gate and (field adj plate)) and align\$8	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/18 12:40
L3	1	gate and (field adj plate) and (tiwn (titanium adj tungsten adj nitride) (tungsten adj titanium adj nitride))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/18 12:44
L4	37	(gate (field adj plate)) and (tiwn (titanium adj tungsten adj nitride) (tungsten adj titanium adj nitride))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/18 12:45
L5	2	(semiconductor substrate wafer silicon) and (gate same (field adj plate) same (tiwn (titanium adj tungsten adj nitride) (tungsten adj titanium adj nitride)))	US-PGPUB; USPAT	OR	ON	2005/04/18 12:49
L6	75	(438/182.ccls. 438/270.ccls. 438/294.ccls. 438/299.ccls. 438/454.ccls. 438/586.ccls. 438/589.ccls.) and (gate same (field adj plate))	US-PGPUB; USPAT	OR	ON	2005/04/18 12:53
L7	16	(semiconductor substrate wafer silicon) and (gate same (field adj plate)) and (aln (aluminum adj nitride))	US-PGPUB; USPAT	OR	ON	2005/04/18 13:00
L8	3	(semiconductor substrate wafer silicon) and (field adj plate) and (aln (aluminum adj nitride))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/18 13:11
L9	111	(438/182.ccls. 438/270.ccls. 438/294.ccls. 438/299.ccls. 438/454.ccls. 438/586.ccls. 438/589.ccls.) and (field adj plate)	US-PGPUB; USPAT	OR	ON	2005/04/18 13:15